

Title of Change: NCV47700/01/10/11 datasheet update Effective date: 1 July 2017 Contact information: Contact your local ON Semiconductor Sales Office or < William.Clemens@onsemi.com> Type of notification: ON Semiconductor will consider this change accepted. Change category: Wafer Fab Change Assembly Change Test Change Other Datasheet Update Change Sub-Category(s): Material Change Shipping/Packaging/Marking Other:
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Example: NCV47701/D, Page 4:
CSO Current at No Load Current $V_{CSO} = 0 \text{ V}, I_{out} = 0 \text{ mA}, (V_{out_norm} = 5 \text{ V})$ I_{CSO_off} - 10 μA REVERSE BIAS CURRENT Reverse Current (Note 11) $V_{in} = 12V, V_{out} = 14 \text{ V}$ I_{out_rev} -40 -25 - mA
THERMAL SHUTDOWN
Thermal Shutdown Temperature I out = 5 mA T SD 150 - 195 °C 9. Measured when the output voltage Vout has dropped -2% from the nominal value obtained at Vin = Vout_nom + 8.5 V. 10. Not guaranteed in dropout. 11. Values based on design and/or characterization. The same update is to be done to the datasheets of the other 3 versions of the NCV477xx family (00/10/11). The change will not impact form, fit, or function of product(s)
List of affected Standard Parts: NCV47700DAJR2G NCV47700PDAJR2G NCV47701DAJR2G NCV47701PDAJR2G NCV47710DAJR2G NCV47711DAJR2G NCV47711DAJR2G